



#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
20V	12.5mΩ @ V <sub>GS</sub> = 4.5V	36A		
200	19mΩ @ V <sub>GS</sub> = 2.5V	30A		

## **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

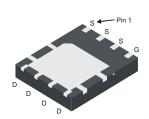
#### **Mechanical Data**

- Case: POWERDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.097 grams (Approximate)

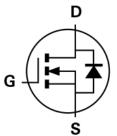
#### POWERDI5060-8



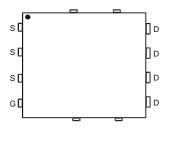
Top View



**Bottom View** 



Internal Schematic



Top View

#### **Ordering Information** (Note 4)

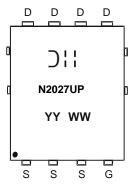
Part Number		Case	Packaging		
	DMN2027UPS-13	POWERDI5060-8	2,500/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**



)¦¦ = Manufacturer's Marking N2027UP = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 15 = 2015) WW = Week (01 - 53)

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Dusin Compant (Nata C) V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	10 8	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	36 29	А
Continuous Dusin Compant (Nata C) V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	8.2 6.6	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 2.5V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	30 23	А
Maximum Continuous Body Diode Forward Currer	Is	60	Α		
Pulsed Drain Current (380µs Pulse, Duty Cycle =	I <sub>DM</sub>	60	А		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	6.8	А		
Avalanche Energy (Note 7) L = 0.1mH	Eas	2.3	mJ		

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		$P_{D}$	1.1	W
The arrest Designation as Austrian (Nets 5)		-	112	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	58	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.9	W
Thermal Desistance Junction to Ambient (Note 6)		D	65	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	34	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	5	°C/W	
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- 7. I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep  $T_J = +25$ °C.



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

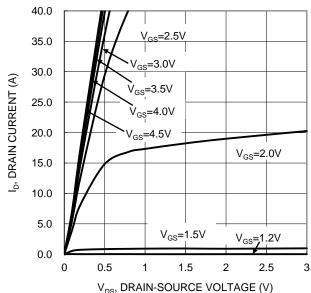
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.7	_	1.3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	_	12.5	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	19		$V_{GS} = 2.5V, I_D = 8.3A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.3	V	$V_{GS} = 0V, I_S = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 9)	•	•		•		•	
Input Capacitance	C <sub>iss</sub>	_	1091	_		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	163	_	pF		
Reverse Transfer Capacitance	Crss	_	148	_			
Gate Resistance	Rq	_	1.5	3.2	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 2.5V)	Qg	_	7.0	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qq	_	11.6	_		101/1	
Gate-Source Charge	Q <sub>gs</sub>	_	2.5	_	nC	$V_{DS} = 10V, I_{D} = 9.4A$	
Gate-Drain Charge	Q <sub>qd</sub>	_	3.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.6	_		$V_{GS} = 4.5V, V_{DS} = 10V,$ $R_{G} = 6\Omega, I_{D} = 1A$	
Turn-On Rise Time	t <sub>R</sub>	_	8.4	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	26.6	_	nS		
Turn-Off Fall Time	t <sub>F</sub>	_	12.6	_	1		
Reverse Recovery Time	t <sub>RR</sub>	_	13.2	_	nS		
Reverse Recovery Charge	Q <sub>RR</sub>	_	7.6	_	nC	$I_F = 12A$ , di/dt = 500A/ $\mu$ s	

Notes:

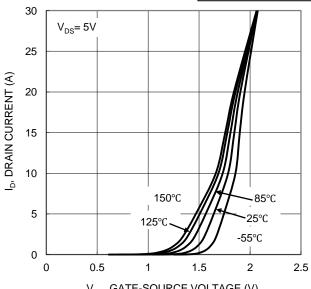
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



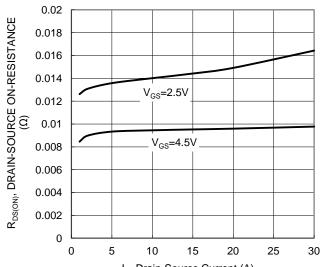
## **DMN2027UPS**



 $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



I<sub>D</sub>, Drain-Source Current (A) Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

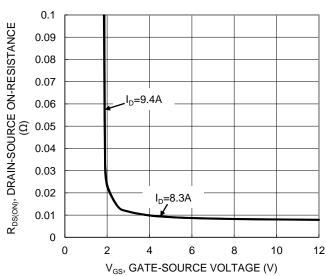
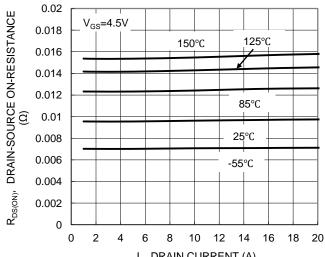
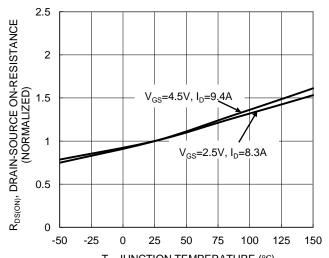


Figure 4. Typical Transfer Characteristic



I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature



T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction Temperature





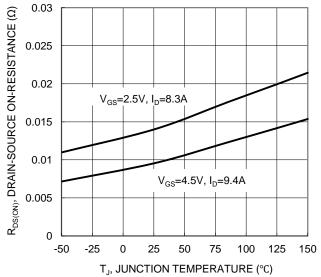


Figure 7. On-Resistance Variation with Junction Temperature

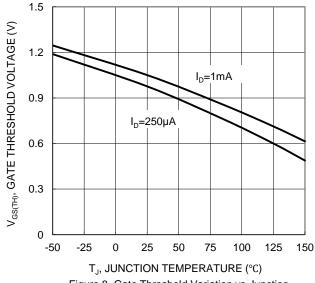


Figure 8. Gate Threshold Variation vs Junction Temperature

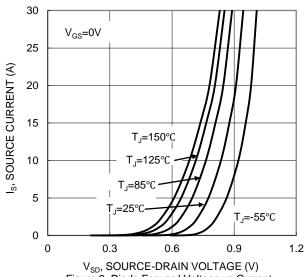
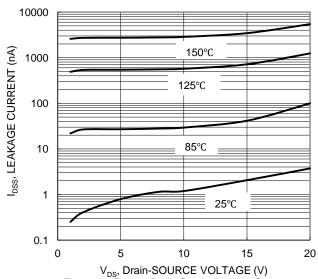


Figure 9. Diode Forward Voltage vs Current



V<sub>DS</sub>, Drain-SOURCE VOLTAGE (V) Figure 10. Typical Drain-Source Leakge Current vs Voltage

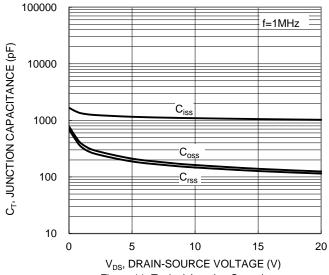
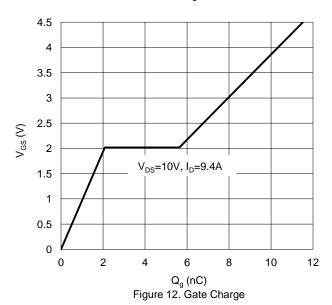
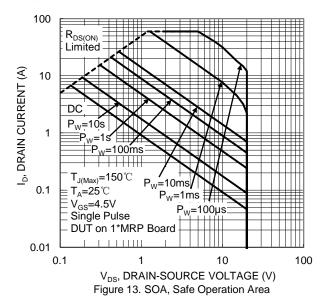
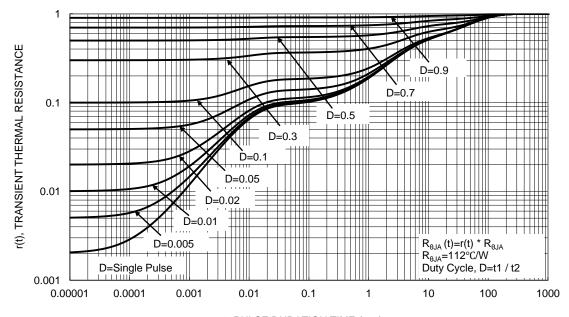


Figure 11. Typical Junction Capacitance









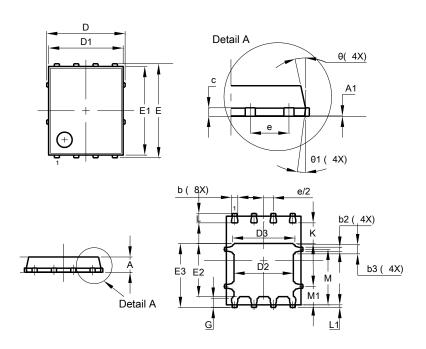
t1, PULSE DURATION TIME (sec) Figure 14 Transient Thermal Resistance



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### POWERDI5060-8

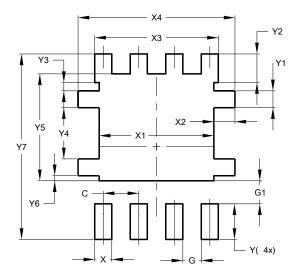


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POWERDI5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
<b>A</b> 1	0.00	0.05	_			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	5	.15 BS	C			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1	.27 BS	С			
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### POWERDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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